

0227273131

(((barrier near (height tunnel)) tunnel\$4 ((energy diagram conduct\$4 gap width) near band) bandgap bandwidth (work adj function))
) near6 erase same ((float\$4 adj (gate electrode plate trap\$4) FG)
)) same (((barrier near (height tunnel)) tunnel\$4 ((energy diagram conduct\$4 gap width) near band) bandgap bandwidth (work adj function))
) near6 retent\$4)

Feb, 2005

Feb, 2003

	U	Inventor	Document/Issue P	Title	Current	Current X	Retrieval S	C	P	Image Do P
1	<input type="checkbox"/>	Chindalore, US	200301:2003:6	Non-volatile memory device with impro	438/20	257/E29.1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030
2	<input type="checkbox"/>	Nakazato, US	657414:2003:1	Memory device using hot charge carri	365/18	257/315,	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 65741
3	<input type="checkbox"/>	Rudeck, Pa	US 200500:2005:2	Methods and structure for an improve	438/26	438/260,	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20050
4	<input type="checkbox"/>	Chindalore, US	200401:2004:6	Non-volatile memory device with impro	257/32	257/321,	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
5	<input type="checkbox"/>	Hyde, John	US 200400:2004:3	Pseudo-nonvolatile direct-tunneling flo	257/31	257/E29.3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
6	<input type="checkbox"/>	Forbes, Le	US 200302:2003:2	Write once read only memory with larg	257/31	257/314,	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030
7	<input type="checkbox"/>	Rudeck, Pa	US 200302:2003:2	Method and structure for an improved	438/20	257/E21.6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030
8	<input type="checkbox"/>	Mihnea, An	US 200300:2003:1	Flash memory cell for high efficiency p	365/18	365/185.0	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030
9	<input type="checkbox"/>	Mihnea, An	US 200300:2003:1	Flash memory cell for high efficiency p	365/18		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030
10	<input type="checkbox"/>	Forbes, Le	US 200201:2002:2	P-channel dynamic flash memory cells	257/31	257/E21.2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020